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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	276480
Number of I/O	444
Number of Gates	1500000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	676-BGA
Supplier Device Package	676-FBGA (27x27)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a3pe1500-1fg676

Table 2-9 • Summary of I/O Output Buffer Power (per pin) – Default I/O Software Settings (continued) (continued)[1]

	C_{LOAD} (pF)	VCCI (V)	Static Power PDC3 (mW)[2]	Dynamic Power PAC10 (µW/MHz)[3]
SSTL3 (I)	30	3.3	26.02	114.87
SSTL3 (II)	30	3.3	42.21	131.76
Differential				
LVDS/B-LVDS/M-LVDS	–	2.5	7.70	89.62
LVPECL	–	3.3	19.42	168.02

Notes:

1. *Dynamic power consumption is given for standard load and software default drive strength and output slew.*
2. *PDC3 is the static power (where applicable) measured on VCCI.*
3. *PAC10 is the total dynamic power measured on VCC and VCCI.*
4. *All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD8-B specification.*

Power Consumption of Various Internal Resources

Table 2-10 • Different Components Contributing to the Dynamic Power Consumption in ProASIC3E Devices

Parameter	Definition	Device-Specific Dynamic Contributions (µW/MHz)		
		A3PE600	A3PE1500	A3PE3000
PAC1	Clock contribution of a Global Rib	12.77	16.21	19.7
PAC2	Clock contribution of a Global Spine	1.85	3.06	4.16
PAC3	Clock contribution of a VersaTile row	0.88		
PAC4	Clock contribution of a VersaTile used as a sequential module	0.12		
PAC5	First contribution of a VersaTile used as a sequential module	0.07		
PAC6	Second contribution of a VersaTile used as a sequential module	0.29		
PAC7	Contribution of a VersaTile used as a combinatorial module	0.29		
PAC8	Average contribution of a routing net	0.70		
PAC9	Contribution of an I/O input pin (standard-dependent)	See Table 2-8 on page 2-6.		
PAC10	Contribution of an I/O output pin (standard-dependent)	See Table 2-9 on page 2-7		
PAC11	Average contribution of a RAM block during a read operation	25.00		
PAC12	Average contribution of a RAM block during a write operation	30.00		
PAC13	Static PLL contribution	2.55 mW		
PAC14	Dynamic contribution for PLL	2.60		

Note: For a different output load, drive strength, or slew rate, Microsemi recommends using the Microsemi power calculator or SmartPower in Libero SoC.

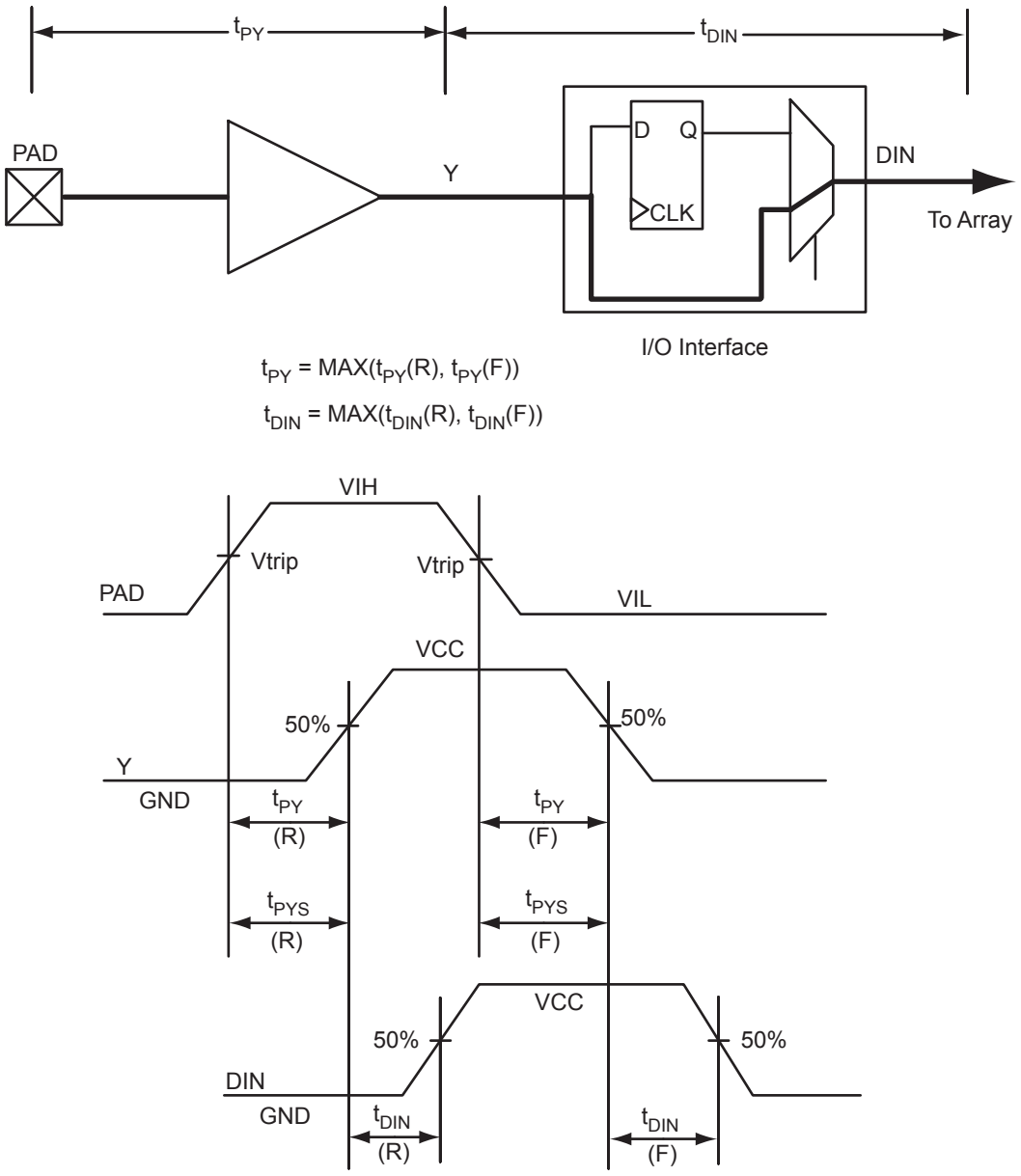


Figure 2-3 • **Input Buffer Timing Model and Delays (example)**

Table 2-19 • I/O Output Buffer Maximum Resistances[1] (continued)

Standard	Drive Strength	$R_{PULL\text{-}DOWN}$ (Ω)[2]	$R_{PULL\text{-}UP}$ (Ω)[3]
3.3 V GTL+	35 mA	12	–
2.5 V GTL+	33 mA	15	–
HSTL (I)	8 mA	50	50
HSTL (II)	15 mA[4]	25	25
SSTL2 (I)	15 mA	27	31
SSTL2 (II)	18 mA	13	15
SSTL3 (I)	14 mA	44	69
SSTL3 (II)	21 mA	18	32

Notes:

1. *These maximum values are provided for informational reasons only. Minimum output buffer resistance values depend on VCCI, drive strength selection, temperature, and process. For board design considerations and detailed output buffer resistances, use the corresponding IBIS models located on the Microsemi SoC Products Group website at www.microsemi.com/index.php?option=com_content&id=1671&lang=en&view=article.*
2. $R_{(PULL\text{-}DOWN\text{-}MAX)}$ = (VOLspec) / IOLspec
3. $R_{(PULL\text{-}UP\text{-}MAX)}$ = (VCCImax – VOHspec) / IOHspec
4. *Output drive strength is below JEDEC specification.*

Table 2-20 • I/O Weak Pull-Up/Pull-Down Resistances
Minimum and Maximum Weak Pull-Up/Pull-Down Resistance Values

	$R_{(WEAK\ PULL\text{-}UP)}$[1] (Ω)		$R_{(WEAK\ PULL\text{-}DOWN)}$[2] (Ω)	
VCCI	Min.	Max.	Min.	Max.
3.3 V	10 k	45 k	10 k	45 k
3.3 V (Wide Range I/Os)	10 k	45 k	10 k	45 k
2.5 V	11 k	55 k	12 k	74 k
1.8 V	18 k	70 k	17 k	110 k
1.5 V	19 k	90 k	19 k	140 k

Notes:

1. $R_{(WEAK\ PULL\text{-}UP\text{-}MAX)}$ = (VCCImax – VOHspec) / $I_{(WEAK\ PULL\text{-}UP\text{-}MIN)}$
2. $R_{(WEAK\ PULL\text{-}DOWN\text{-}MAX)}$ = (VOLspec) / $I_{(WEAK\ PULL\text{-}DOWN\text{-}MIN)}$

Single-Ended I/O Characteristics

3.3 V LVTTL / 3.3 V LVCMOS

Low-Voltage Transistor–Transistor Logic is a general-purpose standard (EIA/JESD) for 3.3 V applications. It uses an LVTTL input buffer and push-pull output buffer. The 3.3 V LVCMOS standard is supported as part of the 3.3 V LVTTL support.

Table 2-25 • Minimum and Maximum DC Input and Output Levels

3.3 V LVTTL / 3.3 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL[1]	IIH[2]
Drive Strength	Min. V	Max. V	Min., V	Max. V	Max. V	Min. V	mA	mA	Max. mA[3]	Max. mA[3]	µA[4]	µA[4]
2 mA	–0.3	0.8	2	3.6	0.4	2.4	4	4	27	25	10	10
4 mA	–0.3	0.8	2	3.6	0.4	2.4	4	4	27	25	10	10
6 mA	–0.3	0.8	2	3.6	0.4	2.4	8	8	54	51	10	10
8 mA	–0.3	0.8	2	3.6	0.4	2.4	8	8	54	51	10	10
12 mA	–0.3	0.8	2	3.6	0.4	2.4	12	12	109	103	10	10
16 mA	–0.3	0.8	2	3.6	0.4	2.4	16	16	127	132	10	10
24 mA	–0.3	0.8	2	3.6	0.4	2.4	24	24	181	268	10	10

Notes:

1. *IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3 V< VIN < VIL.*
2. *IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN< VCCI. Input current is larger when operating outside recommended ranges.*
3. *Currents are measured at high temperature (100°C junction temperature) and maximum voltage.*
4. *Currents are measured at 85°C junction temperature.*
5. *Software default selection highlighted in gray.*

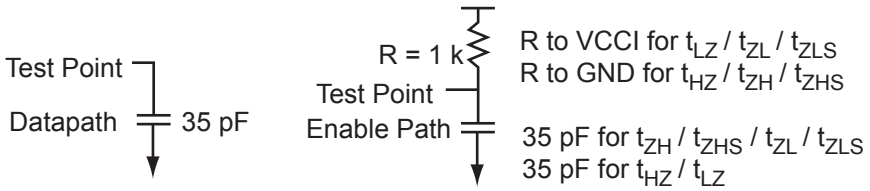


Figure 2-6 • AC Loading

Table 2-26 • 3.3 V LVTTL / 3.3 V LVCMOS AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)	C_{LOAD} (pF)
0	3.3	1.4	–	35

*Note: *Measuring point = Vtrip. See Table 2-15 on page 2-18 for a complete table of trip points.*

Voltage-Referenced I/O Characteristics

3.3 V GTL

Gunning Transceiver Logic is a high-speed bus standard (JESD8-3). It provides a differential amplifier input buffer and an open-drain output buffer. The VCCI pin should be connected to 3.3 V.

Table 2-48 • Minimum and Maximum DC Input and Output Levels

3.3 V GTL	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL	IIH
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA[1]	Max. mA[1]	µA[2]	µA[2]
20 mA[3]	–0.3	VREF – 0.05	VREF + 0.05	3.6	0.4	–	20	20	181	268	10	10

Notes:

1. *Currents are measured at high temperature (100°C junction temperature) and maximum voltage.*
2. *Currents are measured at 85°C junction temperature.*
3. *Output drive strength is below JEDEC specification.*

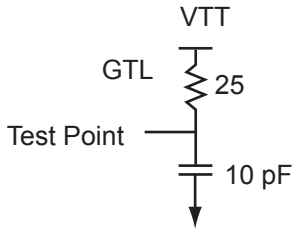


Figure 2-12 • AC Loading

Table 2-49 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)	VTT (typ.) (V)	C_{LOAD} (pF)
VREF – 0.05	VREF + 0.05	0.8	0.8	1.2	10

*Note: *Measuring point = Vtrip. See Table 2-15 on page 2-18 for a complete table of trip points.*

Timing Characteristics

Table 2-50 • 3.3 V GTL
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V VREF = 0.8 V

Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
Std.	0.60	2.08	0.04	2.93	0.43	2.04	2.08			4.27	4.31	ns
–1	0.51	1.77	0.04	2.50	0.36	1.73	1.77			3.63	3.67	ns
–2	0.45	1.55	0.03	2.19	0.32	1.52	1.55			3.19	3.22	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.

3.3 V GTL+

Gunning Transceiver Logic Plus is a high-speed bus standard (JESD8-3). It provides a differential amplifier input buffer and an open-drain output buffer. The VCCI pin should be connected to 3.3 V.

Table 2-54 • Minimum and Maximum DC Input and Output Levels

3.3 V GTL+	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL	IIH
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA[1]	Max. mA[1]	µA[2]	µA[2]
35 mA	–0.3	VREF – 0.1	VREF + 0.1	3.6	0.6	–	35	35	181	268	10	10

Notes:

1. *Currents are measured at high temperature (100°C junction temperature) and maximum voltage.*
2. *Currents are measured at 85°C junction temperature.*

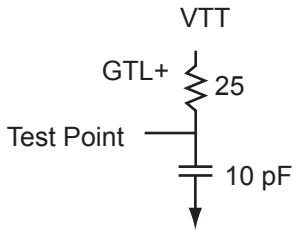


Figure 2-14 • AC Loading

Table 2-55 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)	VTT (typ.) (V)	C_{LOAD} (pF)
VREF – 0.1	VREF + 0.1	1.0	1.0	1.5	10

*Note: *Measuring point = Vtrip. See Table 2-15 on page 2-18 for a complete table of trip points.*

Timing Characteristics

Table 2-56 • 3.3 V GTL+
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V, VREF = 1.0 V

Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
Std.	0.60	2.06	0.04	1.59	0.43	2.09	2.06			4.33	4.29	ns
–1	0.51	1.75	0.04	1.35	0.36	1.78	1.75			3.68	3.65	ns
–2	0.45	1.53	0.03	1.19	0.32	1.56	1.53			3.23	3.20	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.

***Table 2-84* • Parameter Definition and Measuring Nodes**

Parameter Name	Parameter Definition	Measuring Nodes (from, to)*
t_{OCLKQ}	Clock-to-Q of the Output Data Register	H, DOUT
t_{OSUD}	Data Setup Time for the Output Data Register	F, H
t_{OHD}	Data Hold Time for the Output Data Register	F, H
t_{OSUE}	Enable Setup Time for the Output Data Register	G, H
t_{OHE}	Enable Hold Time for the Output Data Register	G, H
t_{OPRE2Q}	Asynchronous Preset-to-Q of the Output Data Register	L, DOUT
$t_{OREMPRE}$	Asynchronous Preset Removal Time for the Output Data Register	L, H
$t_{ORECPRE}$	Asynchronous Preset Recovery Time for the Output Data Register	L, H
t_{OECLKQ}	Clock-to-Q of the Output Enable Register	H, EOUT
t_{OESUD}	Data Setup Time for the Output Enable Register	J, H
t_{OEHD}	Data Hold Time for the Output Enable Register	J, H
t_{OESUE}	Enable Setup Time for the Output Enable Register	K, H
t_{OEHE}	Enable Hold Time for the Output Enable Register	K, H
$t_{OEPRE2Q}$	Asynchronous Preset-to-Q of the Output Enable Register	I, EOUT
$t_{OEREMPRE}$	Asynchronous Preset Removal Time for the Output Enable Register	I, H
$t_{OERECPRE}$	Asynchronous Preset Recovery Time for the Output Enable Register	I, H
t_{ICLKQ}	Clock-to-Q of the Input Data Register	A, E
t_{ISUD}	Data Setup Time for the Input Data Register	C, A
t_{IHD}	Data Hold Time for the Input Data Register	C, A
t_{ISUE}	Enable Setup Time for the Input Data Register	B, A
t_{IHE}	Enable Hold Time for the Input Data Register	B, A
t_{IPRE2Q}	Asynchronous Preset-to-Q of the Input Data Register	D, E
$t_{IREMPRE}$	Asynchronous Preset Removal Time for the Input Data Register	D, A
$t_{IRECPRE}$	Asynchronous Preset Recovery Time for the Input Data Register	D, A

*Note: *See Figure 2-25 on page 2-53 for more information.*

Fully Registered I/O Buffers with Synchronous Enable and Asynchronous Clear

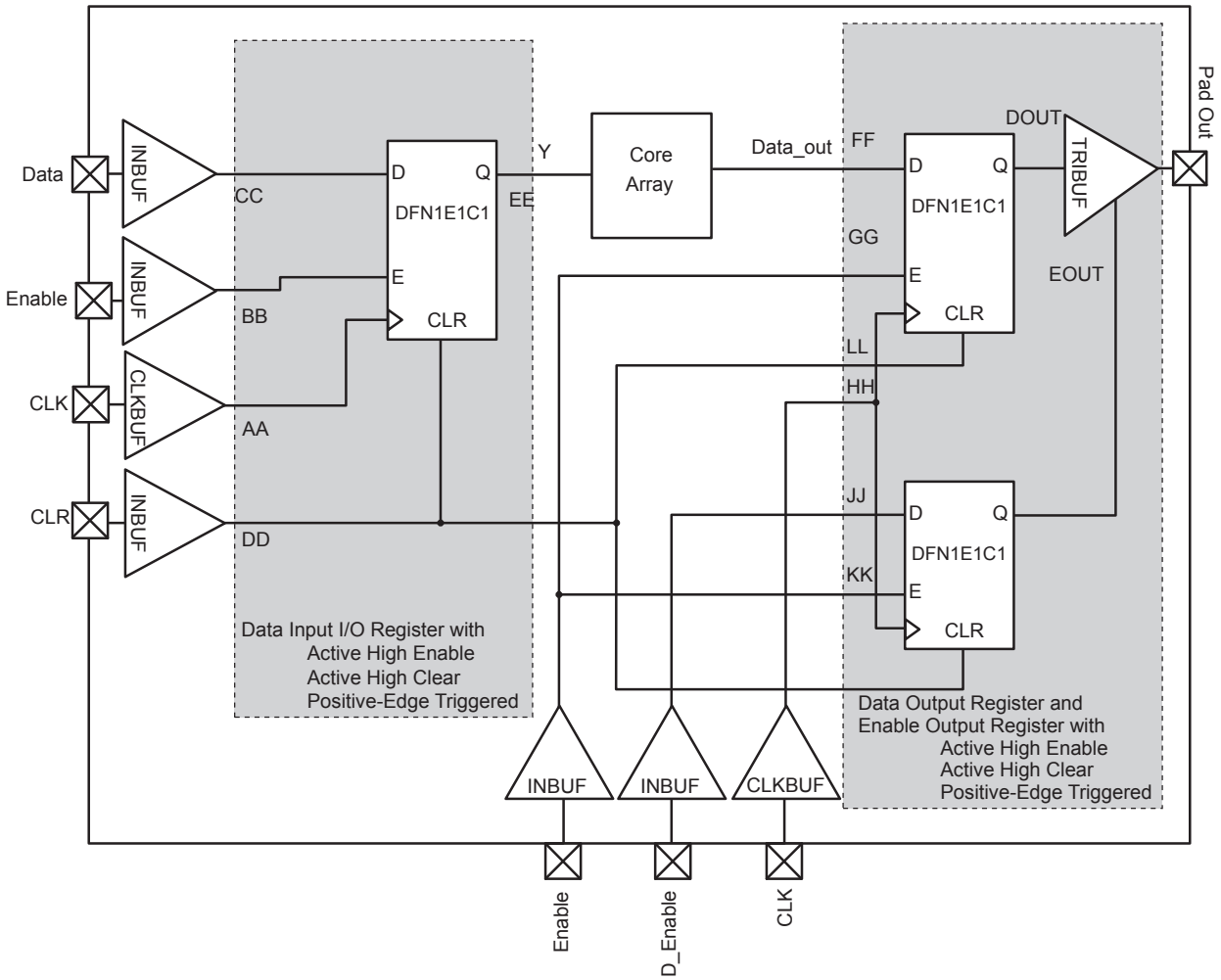


Figure 2-26 • **Timing Model of the Registered I/O Buffers with Synchronous Enable and Asynchronous Clear**

***Table 2-85* • Parameter Definition and Measuring Nodes**

Parameter Name	Parameter Definition	Measuring Nodes (from, to)*
t_{OCLKQ}	Clock-to-Q of the Output Data Register	HH, DOUT
t_{OSUD}	Data Setup Time for the Output Data Register	FF, HH
t_{OHD}	Data Hold Time for the Output Data Register	FF, HH
t_{OSUE}	Enable Setup Time for the Output Data Register	GG, HH
t_{OHE}	Enable Hold Time for the Output Data Register	GG, HH
t_{OCLR2Q}	Asynchronous Clear-to-Q of the Output Data Register	LL, DOUT
$t_{OREMCLR}$	Asynchronous Clear Removal Time for the Output Data Register	LL, HH
$t_{ORECCLR}$	Asynchronous Clear Recovery Time for the Output Data Register	LL, HH
t_{OECLKQ}	Clock-to-Q of the Output Enable Register	HH, EOUT
t_{OESUD}	Data Setup Time for the Output Enable Register	JJ, HH
t_{OEHD}	Data Hold Time for the Output Enable Register	JJ, HH
t_{OESUE}	Enable Setup Time for the Output Enable Register	KK, HH
t_{OEHE}	Enable Hold Time for the Output Enable Register	KK, HH
$t_{OECLR2Q}$	Asynchronous Clear-to-Q of the Output Enable Register	II, EOUT
$t_{OEREMCLR}$	Asynchronous Clear Removal Time for the Output Enable Register	II, HH
$t_{ORECCLR}$	Asynchronous Clear Recovery Time for the Output Enable Register	II, HH
t_{ICLKQ}	Clock-to-Q of the Input Data Register	AA, EE
t_{ISUD}	Data Setup Time for the Input Data Register	CC, AA
t_{IHD}	Data Hold Time for the Input Data Register	CC, AA
t_{ISUE}	Enable Setup Time for the Input Data Register	BB, AA
t_{IHE}	Enable Hold Time for the Input Data Register	BB, AA
t_{ICLR2Q}	Asynchronous Clear-to-Q of the Input Data Register	DD, EE
$t_{IREMCLR}$	Asynchronous Clear Removal Time for the Input Data Register	DD, AA
$t_{IRECCLR}$	Asynchronous Clear Recovery Time for the Input Data Register	DD, AA

*Note: *See Figure 2-26 on page 2-55 for more information.*

Timing Characteristics

Table 2-93 • Combinatorial Cell Propagation Delays
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V

Combinatorial Cell	Equation	Parameter	–2	–1	Std.	Units
INV	Y = !A	t_{PD}	0.40	0.46	0.54	ns
AND2	Y = A · B	t_{PD}	0.47	0.54	0.63	ns
NAND2	Y = !(A · B)	t_{PD}	0.47	0.54	0.63	ns
OR2	Y = A + B	t_{PD}	0.49	0.55	0.65	ns
NOR2	Y = !(A + B)	t_{PD}	0.49	0.55	0.65	ns
XOR2	Y = A ⊕ B	t_{PD}	0.74	0.84	0.99	ns
MAJ3	Y = MAJ(A , B, C)	t_{PD}	0.70	0.79	0.93	ns
XOR3	Y = A ⊕ B ⊕ C	t_{PD}	0.87	1.00	1.17	ns
MUX2	Y = A !S + B S	t_{PD}	0.51	0.58	0.68	ns
AND3	Y = A · B · C	t_{PD}	0.56	0.64	0.75	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.

VersaTile Specifications as a Sequential Module

The ProASIC3E library offers a wide variety of sequential cells, including flip-flops and latches. Each has a data input and optional enable, clear, or preset. In this section, timing characteristics are presented for a representative sample from the library. For more details, refer to the *Fusion, IGLOO/e, and ProASIC3/E Macro Library Guide*.

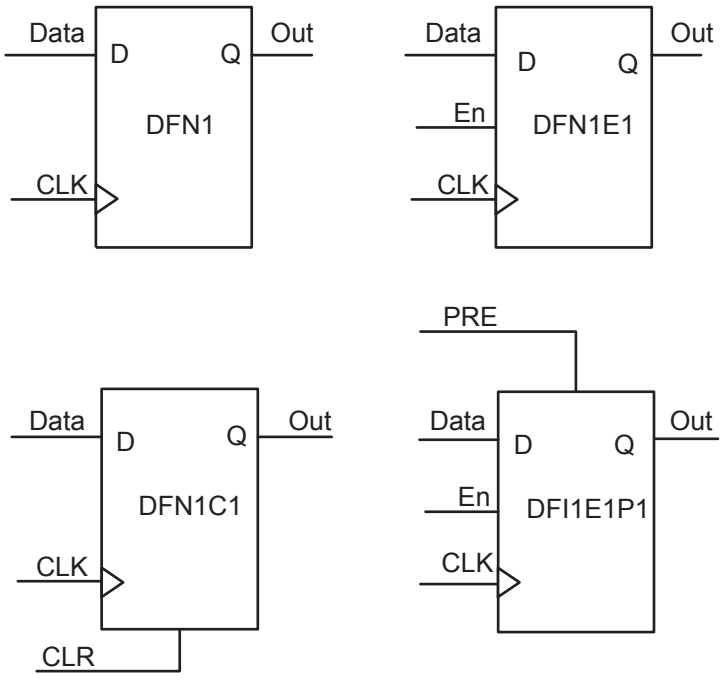


Figure 2-36 • Sample of Sequential Cells

Clock Conditioning Circuits

CCC Electrical Specifications

Timing Characteristics

Table 2-98 • ProASIC3E CCC/PLL Specification

Parameter		Minimum	Typical	Maximum	Units
Clock Conditioning Circuitry Input Frequency f_{IN_CCC}		1.5		350	MHz
Clock Conditioning Circuitry Output Frequency f_{OUT_CCC}		0.75		350	MHz
Delay Increments in Programmable Delay Blocks [1, 2]			160[3]		ps
Serial Clock (SCLK) for Dynamic PLL[4]				125	MHz
Number of Programmable Values in Each Programmable Delay Block				32	
Input Period Jitter				1.5	ns
CCC Output Peak-to-Peak Period Jitter F_{CCC_OUT}		Max Peak-to-Peak Period Jitter			
		1 Global Network Used		3 Global Networks Used	
0.75 MHz to 24 MHz		0.50%		0.70%	
24 MHz to 100 MHz		1.00%		1.20%	
100 MHz to 250 MHz		1.75%		2.00%	
250 MHz to 350 MHz		2.50%		5.60%	
Acquisition Time	LockControl = 0			300	µs
	LockControl = 1			6.0	ms
Tracking Jitter[5]	LockControl = 0			1.6	ns
	LockControl = 1			0.8	ns
Output Duty Cycle		48.5		51.5	%
Delay Range in Block: Programmable Delay 1 [1, 2]		0.6		5.56	ns
Delay Range in Block: Programmable Delay 2 [1,2]		0.025		5.56	ns
Delay Range in Block: Fixed Delay[1,4]			2.2		ns

Notes:

1. *This delay is a function of voltage and temperature. See Table 2-6 on page 2-5 for deratings*
2. *T_J = 25°C, VCC = 1.5 V.*
3. *When the CCC/PLL core is generated by Microsemi core generator software, not all delay values of the specified delay increments are available. Refer to the Libero SoC Online Help for more information.*
4. *Maximum value obtained for a –2 speed-grade device in worst-case commercial conditions. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.*
5. *Tracking jitter is defined as the variation in clock edge position of PLL outputs with reference to the PLL input clock edge. Tracking jitter does not measure the variation in PLL output period, which is covered by the period jitter parameter.*

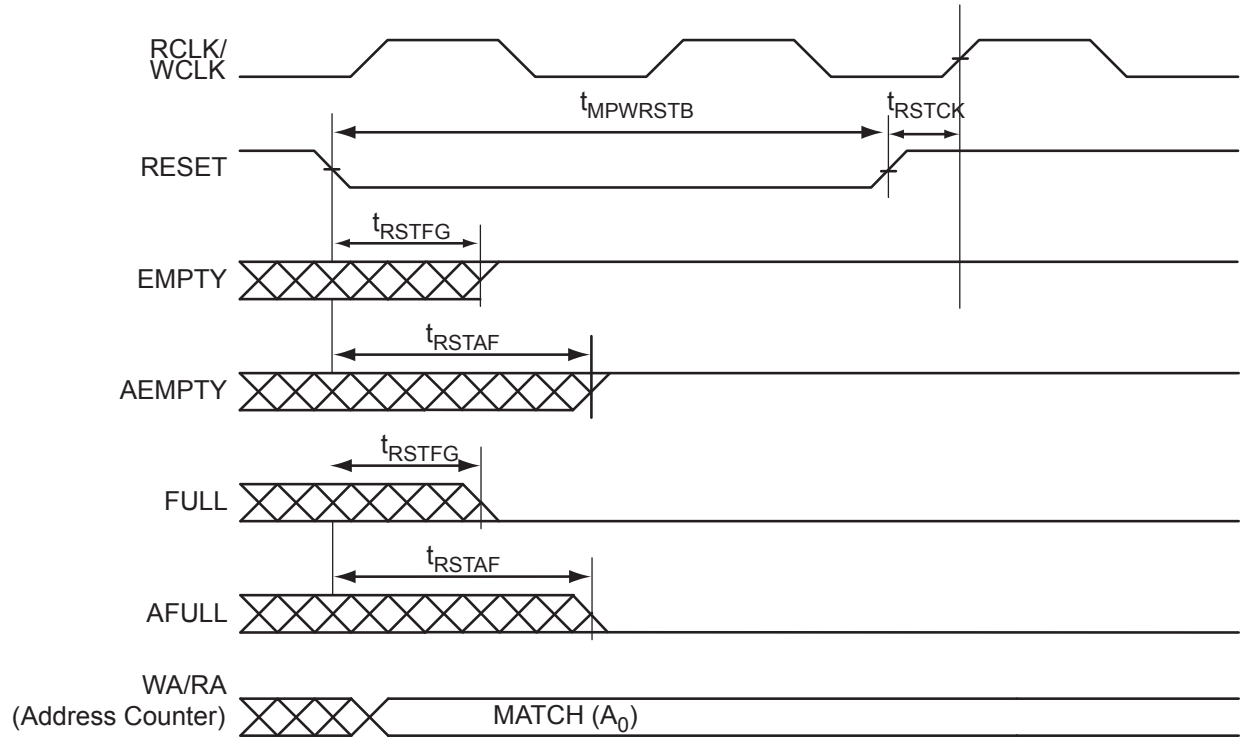


Figure 2-49 • **FIFO Reset**

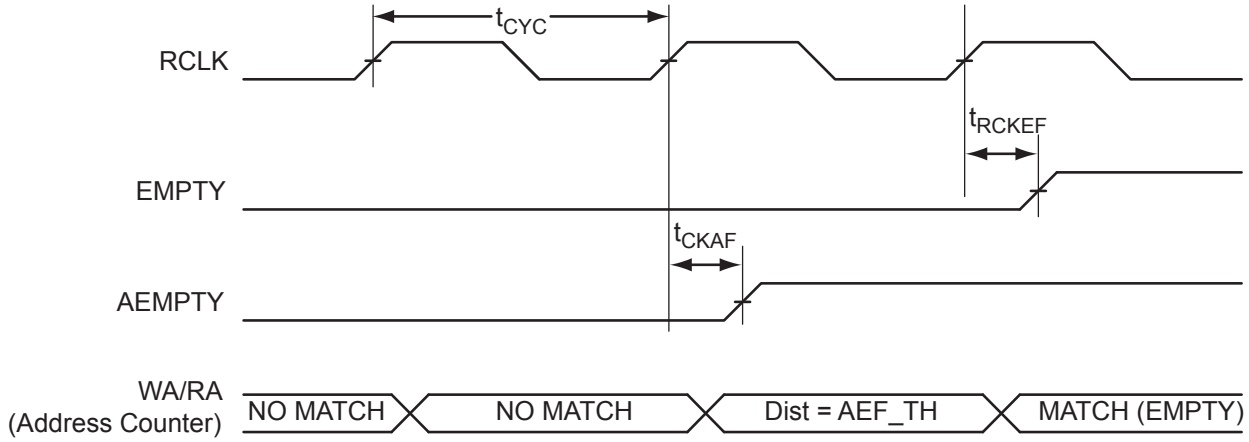
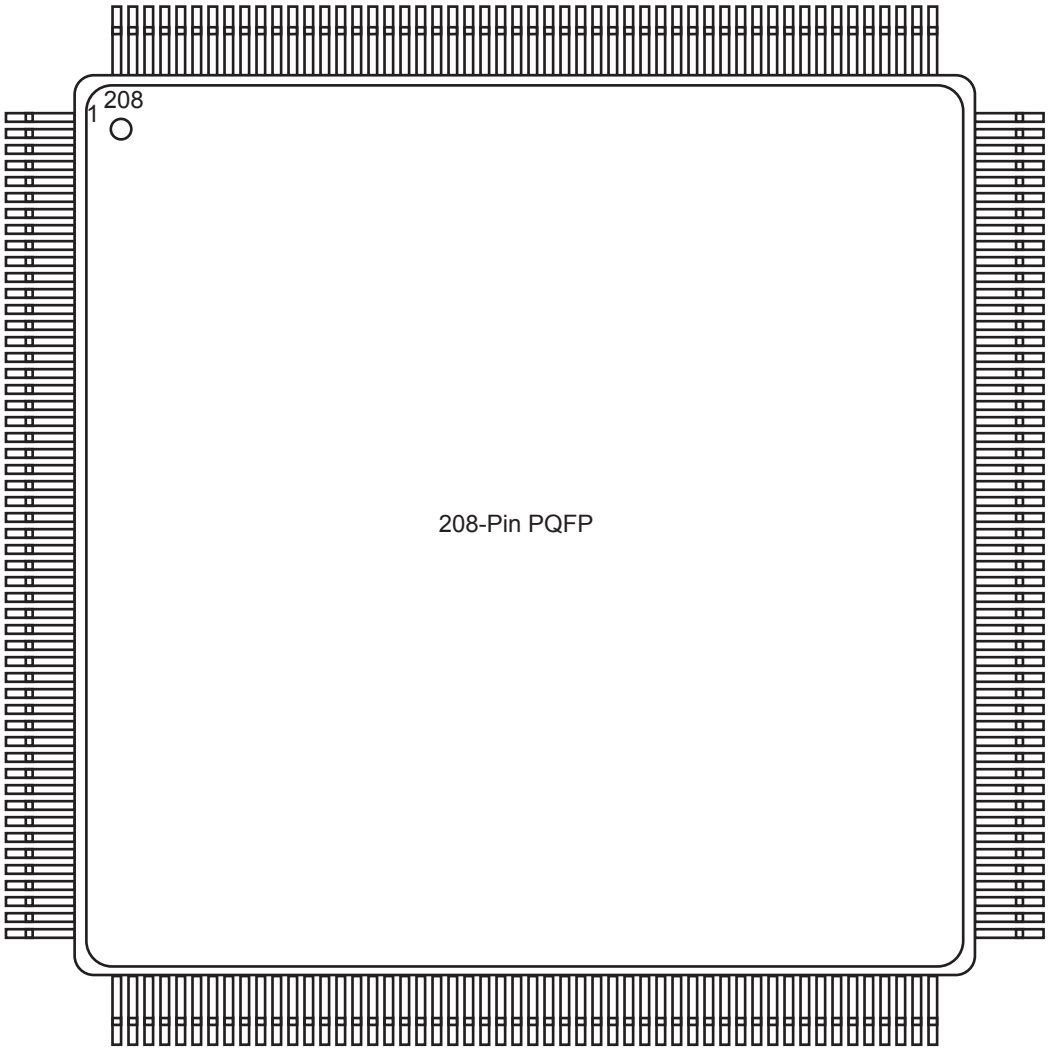


Figure 2-50 • **FIFO EMPTY Flag and AEMPTY Flag Assertion**

4 – Package Pin Assignments

PQ208



Note: This is the top view of the package.

Note

For Package Manufacturing and Environmental information, visit the Resource Center at *http://www.microsemi.com/products/fpga-soc/solutions*.

FG484	
Pin Number	A3PE1500 Function
C21	NC
C22	VCCIB2
D1	NC
D2	NC
D3	NC
D4	GND
D5	GAA0/IO00NDB0V0
D6	GAA1/IO00PDB0V0
D7	GAB0/IO01NDB0V0
D8	IO09PDB0V1
D9	IO13PDB0V1
D10	IO21PDB0V2
D11	IO31NDB0V3
D12	IO37NDB1V0
D13	IO37PDB1V0
D14	IO49NDB1V2
D15	IO49PDB1V2
D16	GBB1/IO56PDB1V3
D17	GBA0/IO57NDB1V3
D18	GBA1/IO57PDB1V3
D19	GND
D20	NC
D21	IO69PDB2V1
D22	NC
E1	NC
E2	IO218PPB7V3
E3	GND
E4	GAB2/IO220PDB7V3
E5	GAA2/IO221PDB7V3
E6	GNDQ
E7	GAB1/IO01PDB0V0
E8	IO09NDB0V1
E9	IO13NDB0V1
E10	IO21NDB0V2
E11	IO31PDB0V3
E12	IO35NDB1V0

FG484	
Pin Number	A3PE1500 Function
E13	IO41NDB1V1
E14	IO41PDB1V1
E15	GBC1/IO55PDB1V3
E16	GBB0/IO56NDB1V3
E17	GNDQ
E18	GBA2/IO58PDB2V0
E19	IO63NDB2V0
E20	GND
E21	IO69NDB2V1
E22	NC
F1	IO218NPB7V3
F2	IO216NDB7V3
F3	IO216PDB7V3
F4	IO220NDB7V3
F5	IO221NDB7V3
F6	VMV7
F7	VCCPLA
F8	GAC0/IO02NDB0V0
F9	GAC1/IO02PDB0V0
F10	IO23NDB0V2
F11	IO23PDB0V2
F12	IO35PDB1V0
F13	IO39NDB1V0
F14	IO45PDB1V1
F15	GBC0/IO55NDB1V3
F16	VCCPLB
F17	VMV2
F18	IO58NDB2V0
F19	IO63PDB2V0
F20	NC
F21	NC
F22	NC
G1	IO211NDB7V2
G2	IO211PDB7V2
G3	NC
G4	IO214PDB7V3

FG484	
Pin Number	A3PE1500 Function
G5	IO217PDB7V3
G6	GAC2/IO219PDB7V3
G7	VCOMPLA
G8	GNDQ
G9	IO19NDB0V2
G10	IO19PDB0V2
G11	IO25PDB0V3
G12	IO33PDB1V0
G13	IO39PDB1V0
G14	IO45NDB1V1
G15	GNDQ
G16	VCOMPLB
G17	GBB2/IO59PDB2V0
G18	IO62PDB2V0
G19	IO62NDB2V0
G20	IO71PDB2V2
G21	IO71NDB2V2
G22	NC
H1	IO209PSB7V2
H2	NC
H3	VCC
H4	IO214NDB7V3
H5	IO217NDB7V3
H6	IO219NDB7V3
H7	IO215PDB7V3
H8	VMV0
H9	VCCIB0
H10	VCCIB0
H11	IO25NDB0V3
H12	IO33NDB1V0
H13	VCCIB1
H14	VCCIB1
H15	VMV1
H16	GBC2/IO60PDB2V0
H17	IO59NDB2V0
H18	IO67NDB2V1

FG484	
Pin Number	**A3PE3000 Function**
V15	IO155NDB4V0
V16	GDB2/IO155PDB4V0
V17	TDI
V18	GNDQ
V19	TDO
V20	GND
V21	IO146PDB3V4
V22	IO142NDB3V3
W1	IO239NDB6V0
W2	IO237PDB6V0
W3	IO230PSB5V4
W4	GND
W5	IO232NDB5V4
W6	GEB2/IO232PDB5V4
W7	IO231NDB5V4
W8	IO214NDB5V2
W9	IO214PDB5V2
W10	IO200NDB5V0
W11	IO192NDB4V4
W12	IO184NDB4V3
W13	IO184PDB4V3
W14	IO156NDB4V0
W15	GDC2/IO156PDB4V0
W16	IO154NDB4V0
W17	GDA2/IO154PDB4V0
W18	TMS
W19	GND
W20	IO150NDB3V4
W21	IO146NDB3V4
W22	IO148PPB3V4
Y1	VCCIB6
Y2	IO237NDB6V0
Y3	IO228NDB5V4
Y4	IO224NDB5V3
Y5	GND
Y6	IO220NDB5V3

FG484	
Pin Number	**A3PE3000 Function**
Y7	IO220PDB5V3
Y8	VCC
Y9	VCC
Y10	IO200PDB5V0
Y11	IO192PDB4V4
Y12	IO188NPB4V4
Y13	IO187PSB4V4
Y14	VCC
Y15	VCC
Y16	IO164NDB4V1
Y17	IO164PDB4V1
Y18	GND
Y19	IO158PPB4V0
Y20	IO150PDB3V4
Y21	IO148NPB3V4
Y22	VCCIB3

FG676	
Pin Number	**A3PE1500 Function**
W25	IO96PDB3V1
W26	IO94NDB3V0
Y1	IO175NDB6V1
Y2	IO175PDB6V1
Y3	IO173NDB6V0
Y4	IO173PDB6V0
Y5	GEC1/IO169PPB6V0
Y6	GNDQ
Y7	VMV6
Y8	VCCIB5
Y9	IO163NDB5V3
Y10	IO159PDB5V3
Y11	IO153PDB5V2
Y12	IO147PDB5V1
Y13	IO139PDB5V0
Y14	IO137PDB5V0
Y15	IO125NDB4V1
Y16	IO125PDB4V1
Y17	IO115NDB4V0
Y18	IO115PDB4V0
Y19	VCC
Y20	VPUMP
Y21	VCOMPLD
Y22	VCCPLD
Y23	IO100NDB3V1
Y24	IO100PDB3V1
Y25	IO96NDB3V1
Y26	IO98PDB3V1

FG896	
Pin Number	**A3PE3000 Function**
AK28	GND
AK29	GND
B1	GND
B2	GND
B3	GAA2/IO309PPB7V4
B4	VCC
B5	IO14PPB0V1
B6	VCC
B7	IO07PPB0V0
B8	IO09PDB0V1
B9	IO15PPB0V1
B10	IO19NDB0V2
B11	IO19PDB0V2
B12	IO29NDB0V3
B13	IO29PDB0V3
B14	IO31PPB0V3
B15	IO37NDB0V4
B16	IO37PDB0V4
B17	IO41PDB1V0
B18	IO51NDB1V1
B19	IO59PDB1V2
B20	IO53PDB1V1
B21	IO53NDB1V1
B22	IO61NDB1V2
B23	IO61PDB1V2
B24	IO69NPB1V3
B25	VCC
B26	GBC0/IO79NPB1V4
B27	VCC
B28	IO64NPB1V2
B29	GND
B30	GND
C1	GND
C2	IO309NPB7V4
C3	VCC
C4	GAA0/IO00NPB0V0

FG896	
Pin Number	**A3PE3000 Function**
C5	VCCIB0
C6	IO03PDB0V0
C7	IO03NDB0V0
C8	GAB1/IO01PDB0V0
C9	IO05PDB0V0
C10	IO15NPB0V1
C11	IO25NDB0V3
C12	IO25PDB0V3
C13	IO31NPB0V3
C14	IO27NDB0V3
C15	IO39NDB0V4
C16	IO39PDB0V4
C17	IO55PPB1V1
C18	IO51PDB1V1
C19	IO59NDB1V2
C20	IO63NDB1V2
C21	IO63PDB1V2
C22	IO67NDB1V3
C23	IO67PDB1V3
C24	IO75NDB1V4
C25	IO75PDB1V4
C26	VCCIB1
C27	IO64PPB1V2
C28	VCC
C29	GBA1/IO81PPB1V4
C30	GND
D1	IO303PPB7V3
D2	VCC
D3	IO305NPB7V3
D4	GND
D5	GAA1/IO00PPB0V0
D6	GAC1/IO02PDB0V0
D7	IO06NPB0V0
D8	GAB0/IO01NDB0V0
D9	IO05NDB0V0
D10	IO11NDB0V1

FG896	
Pin Number	**A3PE3000 Function**
D11	IO11PDB0V1
D12	IO23NDB0V2
D13	IO23PDB0V2
D14	IO27PDB0V3
D15	IO40PDB0V4
D16	IO47NDB1V0
D17	IO47PDB1V0
D18	IO55NPB1V1
D19	IO65NDB1V3
D20	IO65PDB1V3
D21	IO71NDB1V3
D22	IO71PDB1V3
D23	IO73NDB1V4
D24	IO73PDB1V4
D25	IO74NDB1V4
D26	GBB0/IO80NPB1V4
D27	GND
D28	GBA0/IO81NPB1V4
D29	VCC
D30	GBA2/IO82PPB2V0
E1	GND
E2	IO303NPB7V3
E3	VCCIB7
E4	IO305PPB7V3
E5	VCC
E6	GAC0/IO02NDB0V0
E7	VCCIB0
E8	IO06PPB0V0
E9	IO24NDB0V2
E10	IO24PDB0V2
E11	IO13NDB0V1
E12	IO13PDB0V1
E13	IO34NDB0V4
E14	IO34PDB0V4
E15	IO40NDB0V4
E16	IO49NDB1V1

Revision	Changes	Page
Revision 11 (August 2012)	Added a Note stating "VMV pins must be connected to the corresponding VCCI pins. See the "VMVx I/O Supply Voltage (quiet)" section on page 3-1 for further information." to Table 2-1 • Absolute Maximum Ratings and Table 2-2 • Recommended Operating Conditions [1] (SAR 38322).	2-1 3-1 2-1
	The drive strength, IOL, and IOH value for 3.3 V GTL and 2.5 V GTL was changed from 25 mA to 20 mA in the following tables (SAR 31924): "Summary of Maximum and Minimum DC Input and Output Levels" table "Summary of I/O Timing Characteristics—Software Default Settings" table "I/O Output Buffer Maximum Resistances[1]" table "Minimum and Maximum DC Input and Output Levels" table) "Minimum and Maximum DC Input and Output Levels" table Also added note stating "Output drive strength is below JEDEC specification" for Tables 2-17 and 2-19. Additionally, the IOL and IOH values for 3.3 V GTL+ and 2.5 V GTL+ were corrected from 51 to 35 (for 3.3 V GTL+) and from 40 to 33 (for 2.5 V GTL+) in table Table 2-13 (SAR 39714).	 2-16 2-19 2-20 2-39 2-40
	"Duration of Short Circuit Event Before Failure" table was revised to change the maximum temperature from 110°C to 100°C, with an example of six months instead of three months (SAR 37934).	2-22
	The following sentence was deleted from the "2.5 V LVCMOS" section (SAR 34796): "It uses a 5 V–tolerant input buffer and push-pull output buffer." This change was made in revision 10 and omitted from the change table in error.	2-30
Revision 11 (continued)	Figure 2-11 was updated to match tables in the "Summary of I/O Timing Characteristics – Default I/O Software Settings" section (SAR 34889).	2-38
	In Table 2-81 VIL and VIH were revised so that the maximum is 3.6 V for all listed values of VCCI (SAR 37222).	2-52
	Figure 2-47and Figure 2-48 are new (SAR 34848).	2-79
	The following sentence was removed from the "VMVx I/O Supply Voltage (quiet)" section in the "Pin Descriptions and Packaging" chapter: "Within the package, the VMV plane is decoupled from the simultaneous switching noise originating from the output buffer VCCI domain" and replaced with “Within the package, the VMV plane biases the input stage of the I/Os in the I/O banks” (SAR 38322). The datasheet mentions that "VMV pins must be connected to the corresponding VCCI pins" for an ESD enhancement.	3-1

Revision	Changes	Page
Revision 9 (Aug 2009) Product Brief v1.2	All references to speed grade –F have been removed from this document.	N/A
	The "Pro I/Os with Advanced I/O Standards" section was revised to add definitions of hot-swap and cold-sparing.	1-6
DC and Switching Characteristics v1.3	3.3 V LVCMOS and 1.2 V LVCMOS Wide Range support was added to the datasheet. This affects all tables that contained 3.3 V LVCMOS and 1.2 V LVCMOS data.	N/A
	IIL and IIH input leakage current information was added to all "Minimum and Maximum DC Input and Output Levels" tables.	N/A
	–F was removed from the datasheet. The speed grade is no longer supported.	N/A
	In the Table 2-2 • Recommended Operating Conditions [1] "3.0 V DC supply voltage" and note 4 are new.	2-2
	The Table 2-4 • Overshoot and Undershoot Limits [1] table was updated.	2-3
	The Table 2-6 • Temperature and Voltage Derating Factors for Timing Delays table was updated.	2-5
	There are new parameters and data was updated in the Table 2-99 • RAM4K9 table.	2-76
	There are new parameters and data was updated in the Table 2-100 • RAM512X18 table.	2-77
Revision 8 (Feb 2008) Product Brief v1.1	Table 1-2 • ProASIC3E FPGAs Package Sizes Dimensions is new.	1-II
Revision 7 (Jun 2008) DC and Switching Characteristics v1.2	The title of Table 2-4 • Overshoot and Undershoot Limits [1] was modified to remove "as measured on quiet I/Os." Table note 2 was revised to remove "estimated SSO density over cycles." Table note 3 was deleted.	2-3
	Table 2-78 • LVDS Minimum and Maximum DC Input and Output Levels was updated.	2-50
Revision 6 (Jun 2008)	The A3PE600 "FG484" table was missing G22. The pin and its function were added to the table.	4-27
Revision 5 (Jun 2008) Packaging v1.4	The naming conventions changed for the following pins in the "FG484" for the A3PE600: **Pin Number** — **New Function Name** J19 — IO45PPB2V1 K20 — IO45NPB2V1 M2 — IO114NPB6V1 N1 — IO114PPB6V1 N4 — GFC2/IO115PPB6V1 P3 — IO115NPB6V1	4-22
Revision 4 (Apr 2008) Product Brief v1.0	The product brief portion of the datasheet was divided into two sections and given a version number, starting at v1.0. The first section of the document includes features, benefits, ordering information, and temperature and speed grade offerings. The second section is a device family overview.	N/A
Packaging v1.3	The "FG324" package diagram was replaced.	4-12

Datasheet Categories

Categories

In order to provide the latest information to designers, some datasheet parameters are published before data has been fully characterized from silicon devices. The data provided for a given device, as highlighted in the "ProASIC3E Device Status" table on page II, is designated as either "Product Brief," "Advance," "Preliminary," or "Production." The definitions of these categories are as follows:

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The product brief is a summarized version of a datasheet (advance or production) and contains general product information. This document gives an overview of specific device and family information.

Advance

This version contains initial estimated information based on simulation, other products, devices, or speed grades. This information can be used as estimates, but not for production. This label only applies to the DC and Switching Characteristics chapter of the datasheet and will only be used when the data has not been fully characterized.

Preliminary

The datasheet contains information based on simulation and/or initial characterization. The information is believed to be correct, but changes are possible.

Production

This version contains information that is considered to be final.

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